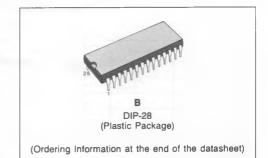
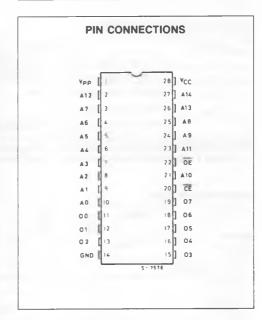


256K (32K × 8) NMOS ONE TIME PROGRAMMABLE ROM

FAST ACCESS TIME: 170ns

- 0 to +70°C STANDARD TEMP. RANGE
- SINGLE + 5V POWER SUPPLY
- ± 10% V_{CC} TOLERANCE AVAILABLE
- LOW STANDBY CURRENT (40mA MAX)
- TTL COMPATIBLE DURING READ AND PROGRAM
- FAST PROGRAMMING ALGORITHM
- ELECTRONIC SIGNATURE



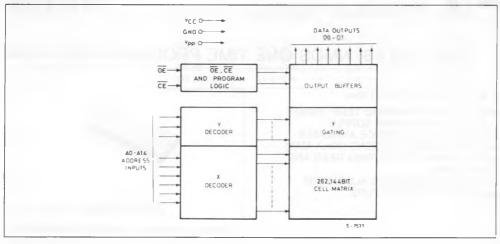


PIN NAMES

A0-A14	ADDRESS INPUT
CE	CHIP ENABLE INPUT
OE	OUTPUT ENABLE INPUT
00-07	DATA INPUT/OUTPUT

The ST27256P is a 262,144-bit one time programmable read only memory (OTP ROM). It is organized as 32.768 words by 8 bits and manufactured using SGS-THOMSON' NMOS-E3 process. The ST27256P with its single + 5V power supply and with an access time of 200ns, is ideal for use with high performance + 5V microprocessor such as Z8, Z80 and Z8000. The ST27256P has an important feature which is to separate the output control, Ouptut Enable (OE) from the Chip Enable control (CE). The OE control eliminates bus contention in multiple bus microprocessor systems. The ST27256P also features a standby mode which reduces the power dissipation without increasing access time. The active current is 100mA while the maximum standby current is only 40 mA, a 60% saving. The standby mode is achieved by applying a TTL-high signal to the CE input. The ST27256P enables implementation of new, advanced systems with firmware intensive architectures. The combination of the ST27256P's high density, and new advanced microprocessors having megabit addressing capability provides designers with opportunities to engineer user-friendly, high reliability, high-performance systems. The ST27256P large storage capability enables it to function as a high density software carrier. Entire operating systems, diagnostics, high-level language programs and specialized application software can reside in a ST27256P directly on a system's memory bus. This permits immediate microprocessor access and execution of software and eliminates the need for time consuming disk accesses and downloads. The ST27256P has an "Electronic Signature" that allows programmers to automatically identify device type and pinout.

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
VI	All Input or Output voltages with respect to ground	+ 6.25 to - 0.6	V
V _{PP}	Supply voltage with respect to ground	+ 14 to - 0,6	V
Tamb	Ambient temperature under bias	- 10 to + 80	°C
T _{stg}	Storage temperature range	- 65 to +125	°C
	Voltage on pin 24 with respect to ground	+ 13.5 to - 0.6	V

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

OPERATING MODES

PINS	CE (20)	OE (22)	A9 (24)	A0 (10)	V _{PP} (1)	V _{CC} (28)	OUTPUTS (11-13, 15-19)
READ	VIL	VIL	X	X	V _{CC}	Vcc	DOUT
OUTPUT DISABLE	VIL	VIH	X	X	V _{CC}	Vcc	HIGH Z
STANDBY	VIH	X	X	X	V _{CC}	Vcc	HIGH Z
PROGRAM	VIL	VIH	X	X	VPP	Vcc	D _{IN}
VERIFY	VIH	VIL	X	X	VPP	Vcc	D _{OUT}
OPTIONAL VERIFY	VIL	VIL	X	X	VPP	Vcc	DOUT
PROGRAM INHIBIT	VIH	VIH	Х	X	V _{PP}	Vcc	HIGH Z
ELECTRONIC SIGNATURE	V _{IL} V _{IL}	V _{IL} V _{IL}	V _H V _H	V _{IL} V _{IH}	V _{CC} V _{CC}	V _{CC} V _{CC}	MAN.CODES DEV.CODE

NOTE: X can be V_{IH} or V_{IL} $V_H = 12V \pm 0.5V$



READ OPERATION

DC AND AC CONDITIONS

Selection Code	– 17X/ – 20X	- 20/ - 25/ - 30
Operating Temperature Range	0 to 70°C	0 to 70°C
V _{CC} Power Supply (1.2)	5V ±5%	5V ± 10%
V _{PP} Voltage (2)	V _{PP} = V _{CC}	V _{PP} = V _{CC}

DC AND OPERATING CHARACTERISTICS

				Values		
Symbol	Parameter	Test Conditions	Min.	Тур. (3)	Max.	Unit
ILI.	Input Load Current	V _{IN} = 5.5V			10	μA
ILO	Output Leakage Current	$V_{OUT} = 5.5V$			10	μA
PP1(2)	VPP Current Read Standby	Vpp = 5.5V			5	mA
ICC1(2)	V _{CC} Current Standby	CE = V _{IH}		20	40	mA
ICC2(2)	V _{CC} Current Active	$\overline{CE} = \overline{OE} = V_{IL}$ $V_{PP} = V_{CC}$		45	100	mA
VIL	Input Low Voltage		- 0.1		+ 0.8	V
VIH	Input High Voltage		2.0		V _{CC} + 1	V
VOL	Output Low Voltage	I _{OL} =2.1 mA			0.45	V
VOH	Output High Voltage	l _{OH} = -400 μA	2.4			V
V _{PP(2)}	V _{PP} Read Voltage	$V_{CC} = 5V \pm 0.25V$	3.8		V _{CC}	V

AC CHARACTERISTICS

		V _{CC} ± 5%	2725	6-17X	2725	6-20X					
Symbol	Parameter	V _{CC} ± 10%			2725	56-20	272	56-25	2725	56-30	Unit
		Test Conditions	Min	Max	Min	Max	Min	Max	Min	Max	
tACC	Address to Output Delay	$\overline{CE} = \overline{OE} = V_{\parallel L}$		170		200		250		300	ns
^t CE	CE to Output Delay	OE = VIL		170		200		250		300	ns
tOE	OE to Output Delay	CE = VIL		70		75		100		120	ns
tDF(4)	OE High to Output Float	CE = VIL		35	0	55	0	60	0	105	ns
tон	Output Hold from Address CE or OE Whichever Occurred First	CE = OE = VIL	0		0		0		0		ns

CAPACITANCE⁽⁵⁾ (T_{amb} = 25°C, f = 1 MHz)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
CIN	Input Capacitance	V _{IN} = 0V		4	6	pF
COUT	Output Capacitance	V _{OUT} = 0V		8	12	pF

Notes:

V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
 V_{PP} may be connected directly to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP1}.
 Typical values are for T_{amb} = 25°C and nominal supply voltages.
 This parameter is only sampled and not 100% tested. Output Float is defined as the point where data is no longer driven-see

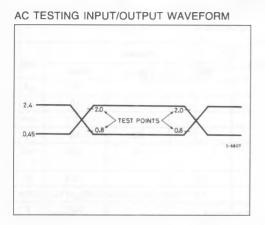
timing diagram

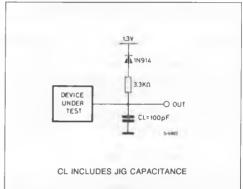
5. This parameter is only sampled and not 100% tested



READ OPERATION (Continued)

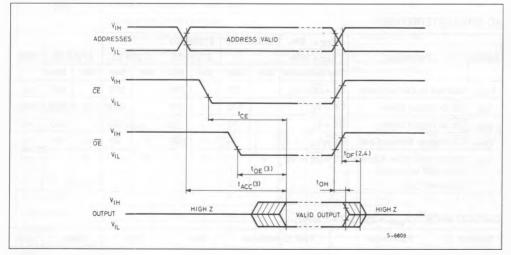
AC TEST CONDITIONS Output Load: 100pF + 1TTL Gate Input Rise and Fall Times: ≤ 20ns Input Pulse Levels: 0.45 to 2.4V Timing Measurement Reference Levels: Inputs 0.8 and 2V Outputs 0.8 and 2V





AC TESTING LOAD CIRCUIT

AC WAVEFORMS



Notes:

- 1. Typical values are for Tamb = 25°C and nominal supply voltage.
- 2. This parameter is only sampled and not 100% tested.
- 3. OE may be delayed up to tACC tOE after the falling edge CE without impact on tACC.
- 4. tDF is specified from OE or CE whichever occurs first.



DEVICE OPERATION

The eight modes of operations of the ST27256P are listed in the Operating Modes. A single 5V power supply is required in the read mode. All inputs are TTL levels except for V_{PP} and 12V on A9 for Electronic Signature.

READ MODE

The ST27256P has two control function, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (CE) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to delay from CE to output (t_{CE}). Data is available at the outputs after the falling edge of OE, assuming that CE has been low and addresses have been stable for at least t_{ACC} - t_{OE} .

STANDBY MODE

The ST27256P has a standby mode which reduces the maximum active power current from 100 mA to 40 mA. The ST27256P is placed in the standby mode by applying a TTL high signal to the CE input. When in the standby mode, the outputs are in a high impedance state, independent of the OE input.

TWO LINE OUTPUT CONTROL

Because OTPs are usually used in larger memory arrays, the product features a 2 line control function which accommodates the use of multiple memory connection. The two line control function allows:

- a) the lowest possible memory power dissipation
- b) complete assurance that output bus contention will not occur.

For the most efficient use of these two control lines, CE should be decoded and used as the primary device selecting function, while OE should be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low power standby mode and that the output pins are only active when data is desired from a particular memory device.

SYSTEM CONSIDERATIONS

The power switching characteristics of NMOS-E3 EPROMs require careful decoupling of the devices. The supply current, I_{CC} , has three segments that are of interest to the system designer: the standby current level, the active current level, and transient current peaks that are produced by the falling and rising edges of CE. The magnitude of this transient

current peaks is dependent on the output capacitive and inductive loading of the device. The associated transient voltage peaks can be suppressed by complying with the two line output control and by properly selected decoupling capacitors. It is recommended that a 1 µF ceramic capacitor be used on every device between V_{CC} and GND. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7 µF bulk electrolytic capacitors should be used between V_{CC} and GND for every eight devices. The bulk capacitor should be located near where the power supply is connected to the array. The purpose of the bulk capacitor is to overcome the voltage drop caused by the inductive effects of PCB traces.

PROGRAMMING

Caution: exceeding 13V on pin 1 (V_{PP}) will damage the ST27256P.

When delivered, all bits of the ST27256P are in the "1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be present in the data word. The ST27256P is in the programming mode when V_{PP} input is at 12.5V and CE and is at TTL low. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL.

FAST PROGRAMMING ALGORITHM

Fast Programming Algorithm rapidly programs ST27256P EPROMs using an efficient and reliable method suited to the production programming environment. Programming reliability is also ensured as the incremental program margin of each bytes is continually monitored to determine when it has been successfully programmed. A flowchart of the ST27256P Fast Programming Algorithm is shown on the last page. The Fast Programming Algorithm utilizes two different pulse types: initial and overprogram. The duration of the initial CE pulse (s) is one millisecond, which will then be followed by a longer overprogram pulse of length 3Xmsec. (X is an iteration counter and is equal to the number of the initial one millisecond pulses applied to a particular ST27256P location), before a correct verify occurs. Up to 25 one-millisecond pulses per byte are provided for before the over program pulse is applied. The entire sequence of program pulses and byte verifications is performed at V_{CC} = 6V and VPP=12.5V. When the Fast Programming cycle has been completed, all bytes should be compared to the original data with $V_{CC} = V_{PP} = 5V$.



DEVICE OPERATION (Continued)

PROGRAM INHIBIT

Programming of multiple ST27256Ps in parallel with different data is also easily accomplished. Except for CE, all like inputs (including OE) of the parallel ST27256P may be common. A TTL low pulse applied to a ST27256P's CE input, with V_{PP} at 12.5V, will program that ST27256P. A high level CE input inhibits the other ST27256Ps from being programmed.

PROGRAM VERIFY

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify is accomplished with OE at V_{II} , CE at V_{IH} and V_{PP} at 12.5V.

OPTIONAL VERIFY

The optional verify may be performed instead of the verify mode. It is performed with OE at V_{IL}, CE at V_{IL} (as opposed to the standard verify which has CE at V_{IH}), and V_{PP} at 12.5V. The outputs will three-state according to the signal presented to OE. Therefore, all devices with V_{PP} = 12.5V and OE = V_{IL} will present data on the bus independent of the CE state. When parallel programming several devices which share the common bus, V_{PP} should be lowered to V_{CC} (= 6V) and the normal read mode used to execute a program verify.

ELECTRONIC SIGNATURE

The Electronic Signature mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C \pm 5°C ambient temperature range that is required when programming the ST27256P. To activate this mode, the programming equipment must force 11.5V to 12.5V on address line A9 (pin 24) of the ST27256P.

Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 (pin 10) from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during Electronic Signature mode. Byte 0 (A0 = V_{IL}) represents the manufacturer code and byte 1 (A0 = V_{IH}) the device identifier code. For the SGS-THOMSON ST27256P, these two identifier bytes are given below.

All identifiers for manufacturer and device codes will possess odd parity, with the MSB (07) defined as the parity bit.

PINS	A0 (10)	07 (19)	O6 (18)	O5 (17)	O4 (16)	O3 (15)	O2 (13)	01 (12)	00 (11)	Hex Data
MANUFACTURER CODE	VIL	0	0	1	0	0	0	0	0	20
DEVICE CODE	VIH	0	0	0	0	0	1	0	0	04

ELECTRONIC SIGNATURE MODE

PROGRAMMING OPERATION $(T_{amb} = 25^{\circ}C \pm 5^{\circ}C, V_{CC}^{(1)} = 6V \pm 0.25V, V_{PP}^{(1)} = 12.5V \pm 0.3V$

DC AND OPERATING CHARACTERISTIC:	DC	AND	OPERATIN	G CHARA	CTERISTIC:
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Question	Deservator	Test Conditions		Unit		
Symbol	Parameter	(See note 1)	Min.	Тур.	Max.	Unit
L	Input Current (All Inputs)	$V_{IN} = V_{IL}$ or V_{IH}			10	μA
VIL	Input Low Level (All Inputs)		- 0.1		0.8	V
VIH	Input High Level		2.0		V _{CC} +1	V
VOL	Output Low Voltage During Verify	I _{OL} = 2.1 mA			0.45	V
VOH	Output High Voltage During Verify	$I_{OH} = -400 \ \mu A$	2.4			V
ICC2	V _{CC} Supply Current (Program & Verify)				100	mA
IPP2	VPP Supply Current (Program)	CE = VIL			50	mA
VID	A9 Electronic Signature Voltage		11.5		12.5	V

AC CHARACTERISTICS

Question	Deserves	Test Conditions		Values		Unit
Symbol	Parameter	(See note 1)	Min.	Тур.	Max.	
tAS	Address Setup Time		2			μS
tOES	OE Setup Time		2			μs
t _{DS}	Data Setup Time		2			μS
t _{AH}	Address Hold Time		0			μS
t _{DH}	Data Hold Time		2			μS
t _{DFP(4)}	Output Enable Output Float Delay		0		130	ns
t _{VPS}	V _{PP} Setup Time		2			μS
t _{VCS}	V _{CC} Setup Time		2			μS
tpw	CE Initial Program Pulse Width	(see Note 3)	0.95	1.0	1.05	ms
topw	CE Overprogram Pulse Width	(see Note 2)	2.85		78.75	ms
tOE	Data Valid from OE				150	ns

Notes:

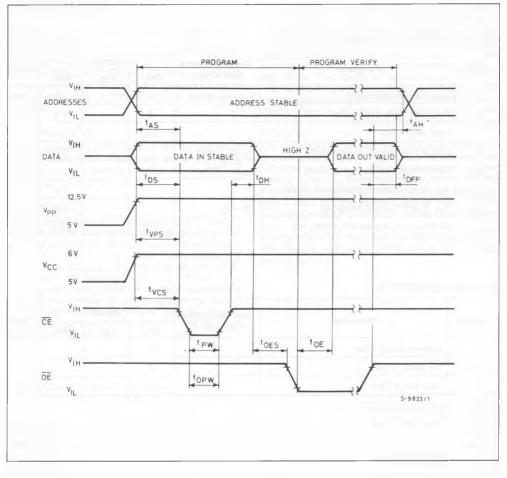
V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
 The length of the overprogram pulse may vary from 2.85msec to 78.75msec as a function of the iteration counter value X.

3. Initial Program Pulse width tolerance is 1msec ±5%.



^{4.} This parameter is only sampled and not 100% tested. Output Float is defined as the point where data is no longer driven (see timing diagram).

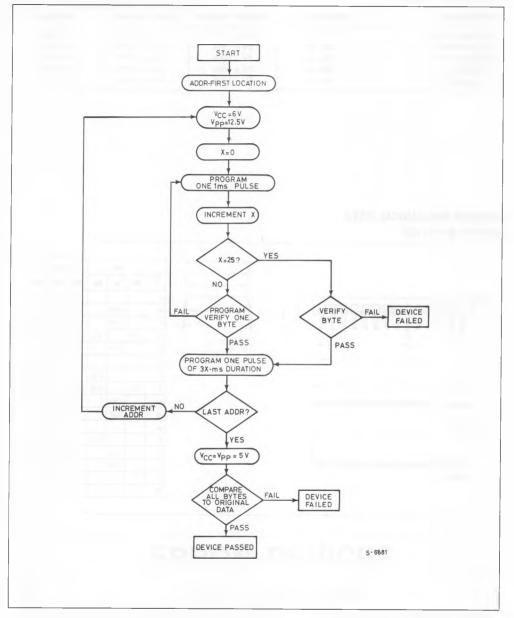
PROGRAMMING WAVEFORMS



Notes:

- The input timing reference level is 0.8V for a V_{IL} and 2V for a V_{IH}.
 t_{DE} and t_{DEP} are characteristics of the device but must be accommodated by the programmer.
 When programming the ST27256P a 0 1_µE capacitor is required across V_{PP} and GROUND to suppress spurious voltage transients which can damage the device.

FAST PROGRAMMING FLOWCHART



ORDERING INFORMATION

Part Number	Access Time	Supply Voltage	Temp. Range	Package
ST27256-17XCP	170 ns	5V ± 5%	0 to +70°C	DIP-28
ST27256-20XCP	200 ns	5V± 5%	0 to + 70°C	DIP-28
ST27256-20CP	200 ns	5V ± 10%	0 to +70°C	DIP-28
ST27256-25CP	250 ns	5V ± 10%	0 to +70°C	DIP-28
ST27256-30CP	300 ns	5V ± 10%	0 to +70°C	DIP-28

PACKAGE MECHANICAL DATA

28-PIN PLASTIC DIP

